

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"20040126992"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 07:06
L2	102	Lim.in. with (Kwan.in. or Yong.in.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 07:07
L3	23	Cho.in. with (Heung.in. with Jae.in.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 07:08
L4	3311	Lee.in. with (Jung.in. or Ho.in.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 07:09
L5	3417	2 or 3 or 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 07:09
L6	120	5 and semiconductor and (gate adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 07:24
L7	59	6 and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 07:11
L8	23	7 and (high with dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 07:21

L9	3	8 and (epi\$4 or epitaxial\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 07:21
L10	26	6 and (epi\$4 or epitaxial\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 07:21
L11	4	10 and (high with dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 07:21

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6	seg and (high with dielectric) and silicate and (SiN or (silicon adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 10:28
L2	101	seg and (high with dielectric) and (SiN or (silicon adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:06
L3	1093	438/39,41,226,478,489.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:05
L4	1434	257/353,354,623.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:05
L5	2613	2 or 3 or 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:05
L6	988	5 and (seg or (epitaxial\$4 with grow\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:18
L7	149	6 and (high with dielectric) and (SiN or (silicon adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:07
L8	48	7 not 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:16

L9	3	"6627488"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:17
L10	9	"6048756"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:17
L11	5	"6184071"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:17
L12	3	"6261911"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:17
L13	3	"6617212"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:17
L14	2	"6664160"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:18
L15	73	8 or 9 or 10 or 11 or 12 or 13 or 14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:18
L16	60	15 and (seg or (epitaxial\$4 with grow\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:29

L17	14	"4820654"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:29
L18	27	"5516710"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:29
L19	15	"6433382"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:29
L20	3	"6544824"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:30
L21	59	17 or 18 or 19 or 20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/23 11:30